

FORM PTO-1449 (Modified)  LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT(S)' INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)	ATTY. DOCKET NO. 6635/60519 (7742-23)	SERIAL NO. 09/997,306
	APPLICANT <b>Yukio HONKAWA, et al.</b>	
	FILING DATE: November 28, 2001	GROUP ART UNIT: 2811



### REFERENCE DESIGNATION

### U.S. PATENT DOCUMENTS

EXAM'R INITIAL	DOCUMENT NUMBER	DATE	NAME	Class	Subclas s	Filing Date If Appropriate
	A1					
	A2					
	A3					
	A4					
	A5					

### FOREIGN PATENT DOCUMENTS

EXAM'R INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	Subclas s	TRANSLAT' N	
						yes	no
	B1	JP-08-288589	11/01/1996	Japan	H01S	3/018	Abstract Only
	B2						
	B3						

### OTHER ART (Include Author, Title, Date, Pertinent Pages, Etc.)

	C1	T. Ohtoshi, et al., "Analysis of Current Leakage in InGaAsP/InP Buried Heterostructure Lasers," IEEE Journal of Quantum Electronics, Vol.25, No.6, June, 1989, pps. 1369-1375.
	C2	
	C3	
	C4	

RECEIVED  
 APR 22 2002  
 TECHNOLOGY CENTER 2800

EXAMINER	DATE CONSIDERED <b>2/6/03</b>
EXAMINER: initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant(s).	

(Information Disclosure Statement — Section 9 PTO-1449 (Modified) [6-1]) IDS 1